

L Number	Hits	Search Text	DB	Time stamp
2	18	117/\$4.cccls. and indium same flux and ("as.sub.4" or "as.sub.2" or arsenic) same flux	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 09:45
3	25	117/\$4.cccls. and inas same ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 09:55
8	30	indium same cell same temperature and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 10:20
12	51	(inas same substrate same temperature) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 11:19
16	22	evaporation same temperature same rate same gaas and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 11:44
-	46	117/\$4.cccls. and gaas and native adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 13:53
-	19	117/\$4.cccls. and gaas and (desorp\$4 same (arsenic or "as.sub.2" or "as.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:03
-	187	117/\$4.cccls. and super\$llattice and (gaas same substrate) and @py<2001	USPAT; US-PGFUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:32
-	40	117/\$4.cccls. and super\$llattice and (gaas same substrate) and @py<2001 and inas	USPAT; US-PGFUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:35
-	25	117/\$4.cccls. and super\$llattice and (gaas same substrate) and @py<2001 and inas and mbe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 14:38
-	60	(gaas same substrate) and inas and buffer and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/18 15:41
-	83	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness and 117/\$4.cccls.	USPAT; US-PGFUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:23
-	48	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness same temperature and 117/\$4.cccls.	USPAT; US-PGFUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:29

	150	117/\$4.cccls. and amorphous and anneal\$3 and gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:30
	63	117/\$4.cccls. and amorphous same anneal\$3 and gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 10:32
	54	117/\$4.cccls. and (ga or gallium) same cell same temperature and mbe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:22
	44	117/\$4.cccls. and gaas same buffer and inas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:29
	12	117/\$4.cccls. and evaporate same temperature same arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:50
	63	117/\$4.cccls. and evaporat\$3 same temperature same arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 13:50
	186	117/\$4.cccls. and single adj crystal same amorphous and gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 15:31
	57	117/\$4.cccls. and single adj crystal same amorphous same gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 16:11
	190	117/\$4.cccls. and low adj temperature same gaas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 16:17
	30	117/\$4.cccls. and low adj temperature same gaas same pressure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/19 16:14
	165	117/\$4.cccls. and gaas same pressure and mbe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/22 09:39